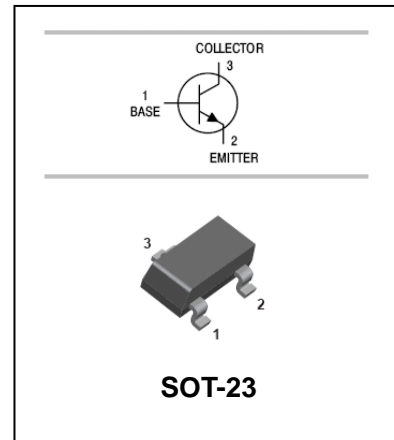


Silicon Epitaxial Planar Transistor

2SC2412

FEATURES

- Low $C_{ob}, C_{ob}=2.0Pf$
- Complementary to 2SA1037



APPLICATIONS

- NPN Silicon Epitaxial Planar Transistor

ORDERING INFORMATION

Type No.	Marking	Package Code
2SC2412	BQ,BR,BS	SOT-23

MAXIMUM RATING @ $T_a=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current -Continuous	150	mA
P_C	Collector Dissipation	200	mW
T_j, T_{stg}	Junction and Storage Temperature	-55~150	$^{\circ}C$

Silicon Epitaxial Planar Transistor**2SC2412****ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu A, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\mu A, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu A, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=60V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=6V, I_C=1mA$	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50mA, I_B=5mA$			0.4	V
Collector output capacitance	C_{ob}	$V_{CB}=12V, I_C=-2mA,$ $f=100MHz$		2.0		pF
Transition frequency	f_T	$V_{CE}=12V, I_C=2mA$ $f=100MHz$		180		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	Q	R	S
Range	120-270	180-390	270-560
Marking	BQ	BR	BS

Silicon Epitaxial Planar Transistor

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TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

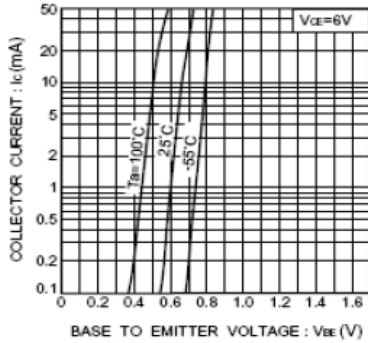


Fig.1 Grounded emitter propagation characteristics

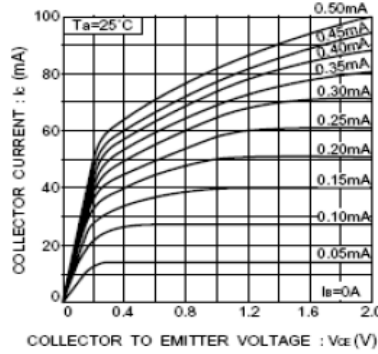


Fig.2 Grounded emitter output characteristics (I)

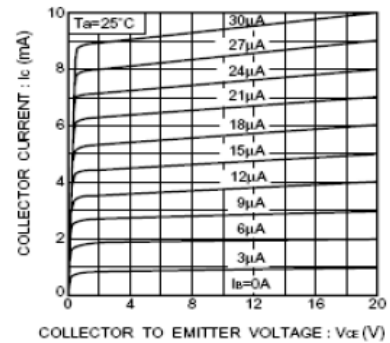


Fig.3 Grounded emitter output characteristics (II)

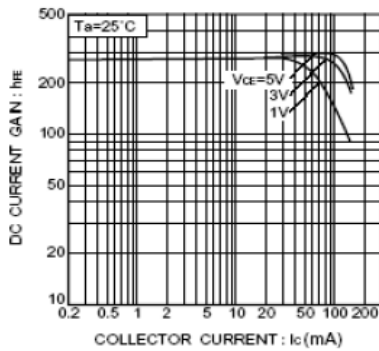


Fig.4 DC current gain vs. collector current (I)

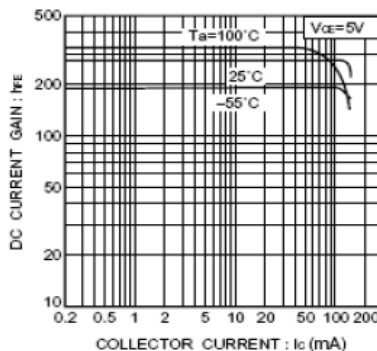


Fig.5 DC current gain vs. collector current (II)

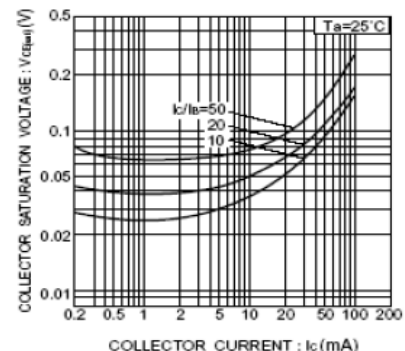


Fig.6 Collector-emitter saturation voltage vs. collector current

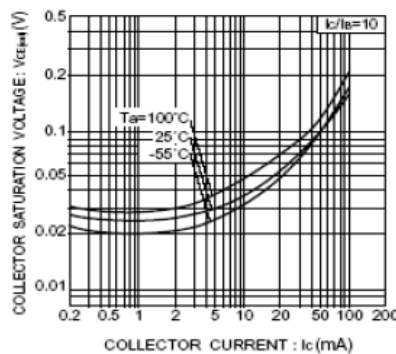


Fig.7 Collector-emitter saturation voltage vs. collector current (I)

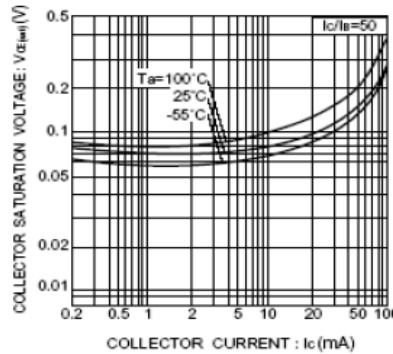


Fig.8 Collector-emitter saturation voltage vs. collector current (II)

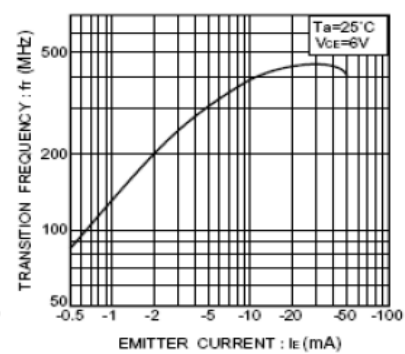


Fig.9 Gain bandwidth product vs. emitter current

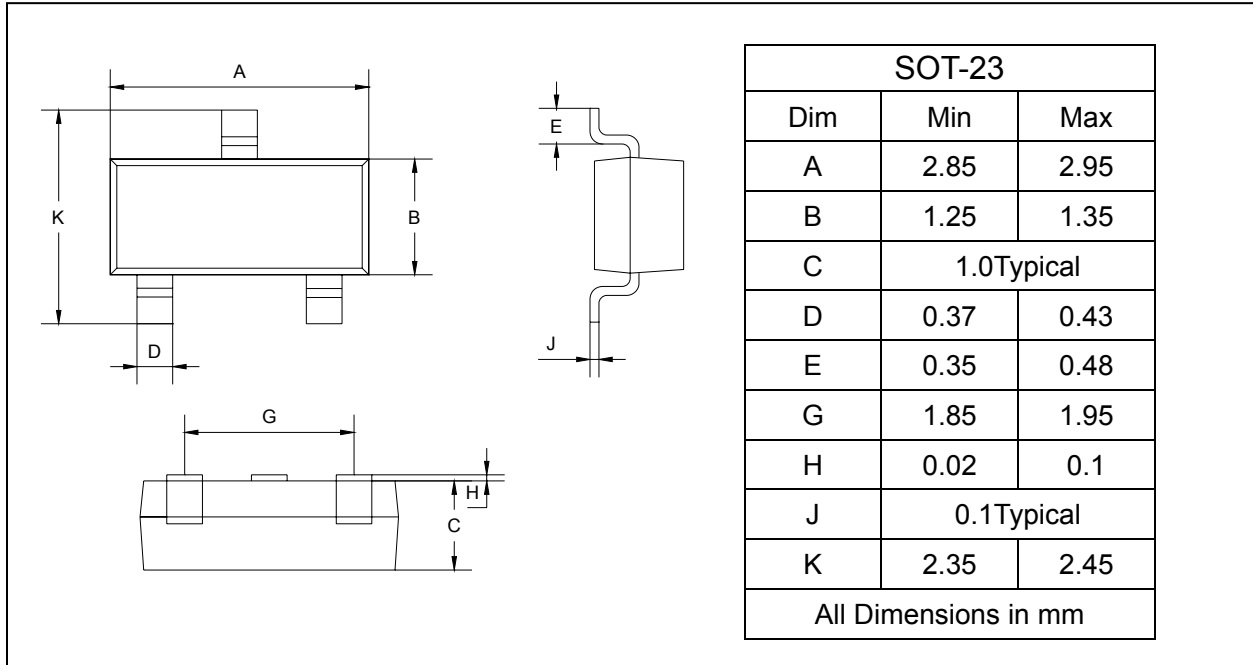
Silicon Epitaxial Planar Transistor

2SC2412

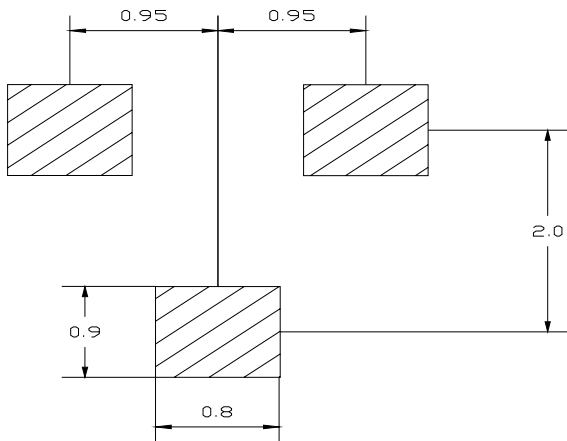
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
2SC2412	SOT-23	3000/Tape&Reel